wish out the semiconductor products and ets semicon ductor product & Intel corporation microprocessors, chipsets and other components for and tregarency - me samsung Electronics -(m) Tarwan semi conductor microprocessors, graphic facturing company processors - dynamic - access memory (DRAM) and NAND flash memory. tochnology DRAM, NAND flash memory (Micron technology microprocessors, chipsets. (1) Broad com Inc (m) Texas instruments - microcontrollers, amplifiers and components for a wide Inc The - microprocessors, modems (1) Qualcomm Inc me crocontrollers, automotive (x) NXP semiconductors (1) Infineon technologies + power management chips - Graphic processor, gaming it Nyidea corporation apo @ What are the elifferent , et icles availed in also field a

@ what are the latest captop processors from Amp Intel and Apple: Frequency and node 3: (1) Intel - version 13th - Generation core 99-13900k Frequency - 6.8 to 6.0 4H2 Theres and processor nodo 10 nm - 24 cores. (:1) AMD Ryzentag - By AMD - frequency - 4.0 9 Hz can semitiondater - microprocessors graphie - m1 max - frequency - 3228 gitt (ii) Apple - monorous and plane flore memory. @ What are the latest mobile processor available from Qualcomm and mediatet; Frequency and noder. Jargania (v) Breadcom Inc D. alcomm - snapdragon 8 gen 3 (:) Qualcomm - shapangy - 3.3 a Hs mostrostique & modes - 4 mm 2 snadragon 86+59 frequency - 3.19th nodes - 4nm systematics; automostics (ii) medrateke Dimensity 9300-by mediatek - frequency - 3.25 a Hz nodes unmandet noon fait (.) , me deatek pimensity 2000 - fraquency - nodes to 4 nm 090 What are the different job roles available in vist field. As (:) VL SI Design Engineer

(7) physical Design Engeneer (11) Verification Engineer 100 (10) ASIC Design Engineer (v) Digetal Design Engeneer (vi) layout Engineer som who examined great we (M:) FRGA Design Engineer (MI) Ichoesign Engineer was that he mad whom (VI) DET (Design For Test) Engineer pularized is the acity report Mos based B Difference between MOSFET and FINFET and why shift from BJT to MOSFET TO FINFET MOSFETS FINEETS · Mosfets are planar devices · Fin FETs are three dimensio -nal structures with with metal, oxide and sem: conductors involved in vertical fins forming a their basic structure. drain and source . In prosfet double partern In FINFET we are using is not necessary. a double pattern * MOSFETS have a low gate-to Finfets have a higher gate - to- source voltage · MOSFETS use high FINFETS use less electricity because their gate capacitance electricity. is lower than than that of MOSFETS · mosfET fabrication is FINFET fabrication es easy compare to Jabr FINFET different . As chips are downsited, transistors also shrint. this compactness brings the drain and source closer and control over the channel carrier reduces the gate this type of short channel effect can eause

serious Essues in Mosfets, The prensence of geves FYNFETS better short-channel behaviour. in the constant Engineer 6 Evolution of memory technology: By: The single transistor DRAM cell was developed in 1966. for roward by a mos developed in 1966, followed by a mos sensionductor device used to create por en 1964. From 1968 to the early 1970s. N-type mos inmos) meniony also started to become popularited, By the early 1970s, mas based memory started becoming much more widely used served range of memory a property of the server of the server. printary secondary memory magnetec | Flash tape memory ran rom magnetic némon FOO Hon slivery o PROM EPROM EPROM ED DUP BED HUD the feet use less decentable a mosters wie his typour of a heavest their gate capacitans is course than them that 27 notherward to 197 some O AUGSFETS cash constituted to trape significan thefer tobulation the part forming one employees to be standard and replace the the patences to age the deal age of course to an age of the course and to descent the course age of th